

N-channel 100 V 9.6 m Ω standard level MOSFET in D2PAK

Rev. 2 — 2 March 2012

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	89	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	211	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	8.16	9.6	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I_{D} = 60 A; V_{DS} = 50 V;	-	23	-	nC
Q _{G(tot)}	total gate charge	see Figure 14;see Figure 15	-	82	-	nC
	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^{\circ}C; \ I_{D} = 89 \ A; \\ V_{sup} \leq 100 \ V; \ unclamped; \ R_{GS} = 50 \ \Omega \end{array}$	-	-	177	mJ

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN9R5-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

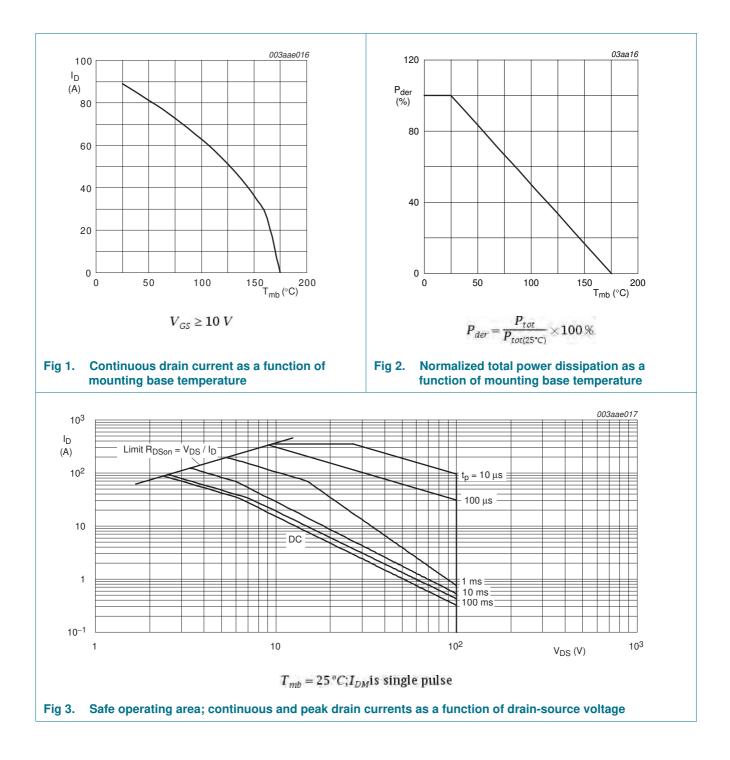
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	63	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	89	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 3</u>	-	355	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	211	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	diode				
ls	source current	T _{mb} = 25 °C	-	89	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	355	А
Avalanche ru	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 89 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω	-	177	mJ

PSMN9R5-100BS



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Thermal characteristics 5.

Table 5.	Inermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.38	0.71	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

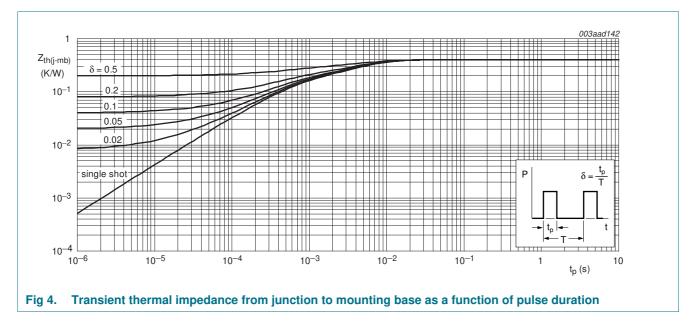


Table 5 The wood all encode visiting

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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	4.8	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 125 °C	-	-	100	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	4	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 12</u>	-	-	17.3	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u>	-	23.5	27.4	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	8.16	9.6	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.7	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$\begin{split} I_D &= 0 \text{ A}; V_{DS} = 0 V; V_{GS} = 10 V; \\ \text{see } \frac{\text{Figure } 14}{\text{Figure } 14} \end{split}$	-	67	-	nC
		$I_D = 60 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	82	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	21	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 60 \text{ A}; \text{V}_{DS} = 50 \text{V}; \text{V}_{GS} = 3 \text{V};$ see Figure 14	-	13.1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge	$I_D = 60 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	7.8	-	nC
Q _{GD}	gate-drain charge	$I_D = 60 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	23	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.5	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4454	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	302	-	pF
C _{rss}	reverse transfer capacitance		-	185	-	рF
d(on)	turn-on delay time	$V_{DS} = 50 \ V; \ R_L = 0.8 \ \Omega; \ V_{GS} = 10 \ V;$	-	22	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; T_j = 25 \ ^{\circ}C$	-	25.2	-	ns
t _{d(off)}	turn-off delay time		-	52.2	-	ns
t _f	fall time		-	22.8	-	ns

Symbol

PSMN9R5-100BS

Тур

Unit

Max

N-channel 100 V 9.6 mΩ standard level MOSFET in D2PAK

Min

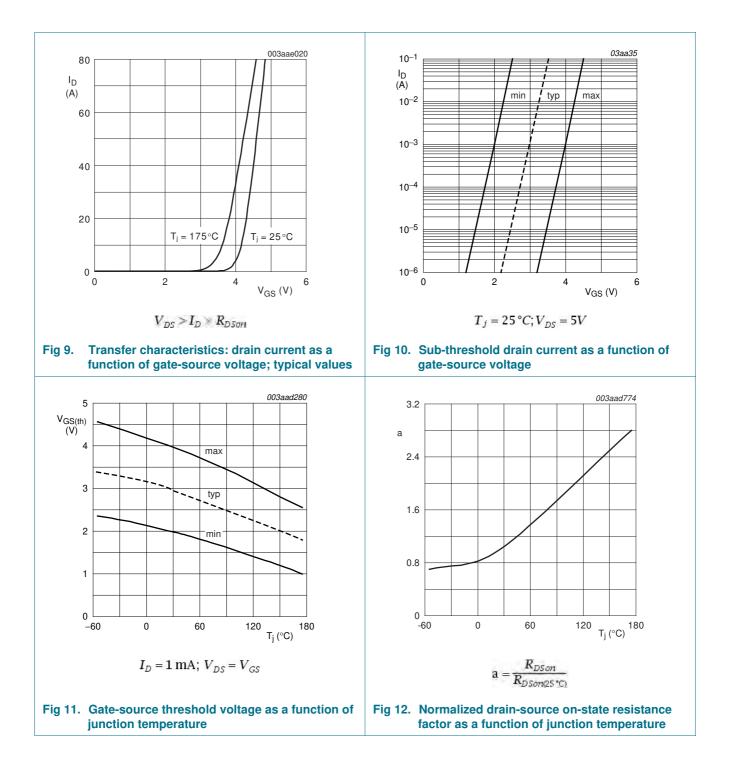
urce-draii	luiuue					
D	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 17	-	0.85	1.2	V
	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 100 \text{ A}/\mu\text{s}; V_{GS} = 100 \text{ A}/\mu\text{s}; V_{GS}$	= 0 V; -	61.5	-	ns
	recovered charge	V _{DS} = 50 V	-	157	-	nC
30		003aae025 8000			003aae022	
R _{DSon} (mΩ)		C C				
(11152)		(pF)			C _{iss}	
24		6000				
4						
18		4000			C _{rss}	
H					133	
12		2000				
12		2000				
6		o				
4	8 12	16 V _{GS} (V) 20 0	3 6	9 V	12/ _{GS} (V)	
u 5. Dra	$T_j = 25 \ ^\circ C; I_D = 20$	A	$V_{DS} = 0V; f =$		citances	s as a
	$T_j = 25 \ ^\circ C; I_D = 20$ nin-source on-state resist pate-source voltage; typic	A ance as a function Fig 6. Inp	$V_{DS} = 0V; f =$ ut and reverse trans ction of gate-source	sfer capa		
of g	in-source on-state resist	A ance as a function Fig 6. Inp fun	ut and reverse trans	sfer capa e voltage;		
	in-source on-state resist	A ance as a function Fig 6. Inp fun	ut and reverse trans	sfer capa e voltage;	; typical	
0f ç 150 g _{fs}	in-source on-state resist	A ance as a function Fig 6. Inp fun	ut and reverse trans ction of gate-source	sfer capa e voltage;	typical	
of <u>c</u>	in-source on-state resist	A ance as a function fun	ut and reverse trans ction of gate-source	sfer capa e voltage;	typical	
0f ç 150 g _{fs}	in-source on-state resist	A ance as a function cal values Fig 6. Inp fun	ut and reverse trans ction of gate-source	sfer capa e voltage;	typical	
0f g 150 g _{fs} (S)	in-source on-state resist	A ance as a function cal values Fig 6. Inp fun	ut and reverse trans ction of gate-source	sfer capa e voltage;	5 4.8	
0f g 150 g _{fs} (S)	in-source on-state resist	A ance as a function cal values Fig 6. Inp fun	ut and reverse trans ction of gate-source	sfer capa e voltage;	5	
0f g 150 g _{fs} (S)	in-source on-state resist	A ance as a function cal values	ut and reverse trans ction of gate-source	sfer capa e voltage;	5 4.8 4.7	
0f g 150 g _{fs} (S)	in-source on-state resist	A ance as a function cal values	ut and reverse trans ction of gate-source	sfer capa e voltage;	5 4.8	
of g 150 g _{fs} (S) 100	in-source on-state resist	A ance as a function cal values	ut and reverse trans ction of gate-source	sfer capa e voltage;	5 4.8 4.7	
of g 150 g _{fs} (S) 100	in-source on-state resist	A ance as a function cal values	ut and reverse trans ction of gate-source	e voltage;	2003aae019 5 4.8 4.7 4.5 4.3	
of g 9fs (S) 100 50	in-source on-state resist	A ance as a function cal values	ut and reverse trans ction of gate-source	e voltage;	2003aae019 5 4.8 4.7 4.5	
of g 150 g _{fs} (S) 100	ain-source on-state resist.	A ance as a function cal values	ut and reverse trans ction of gate-source	e voltage;	2003aae019 5 4.8 4.7 4.5 4.3	
of g 150 9 _{fs} (S) 100 50 0	ain-source on-state resist.	A ance as a function bal values 003aae021 (A) (10 5.5	e voltage;	2003aae019 5 4.8 4.7 4.5 4.3 6 (V) = 4	
of g 150 g _{fs} (S) 100 50 0 0	20 40	A ance as a function al values 100 10 10 10 (A) 75 50 25 0 25 0 0 10 (A) 75 50 25 0 0 0 25 0 0 0 0 0 0 0 0	10 5.5	e voltage;	$\frac{4.8}{4.7}$ 4.5 4.3 4.5 4.3 $V_{DS}(V)^{2}$	value

Table 6. Characteristics ...continued

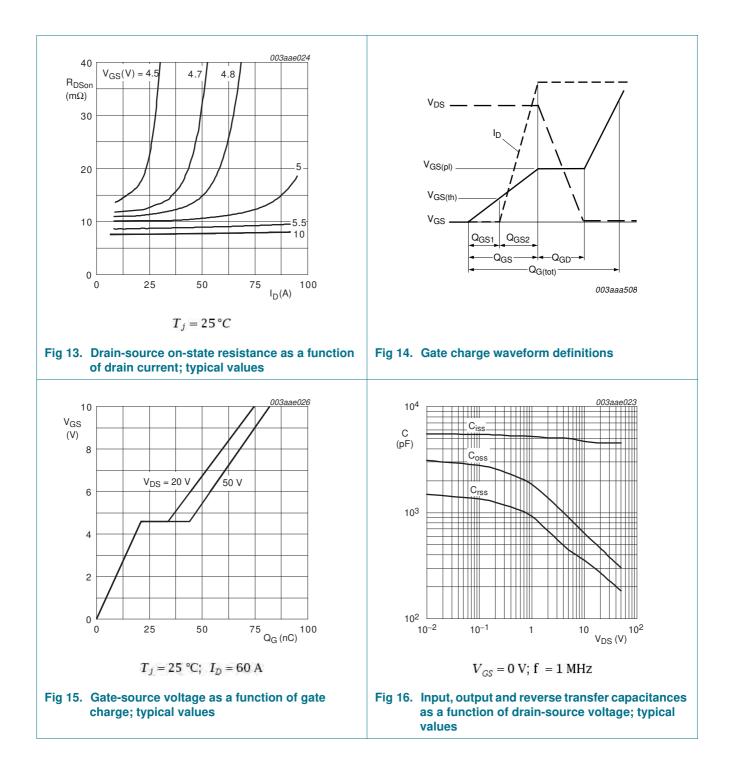
Parameter

Conditions

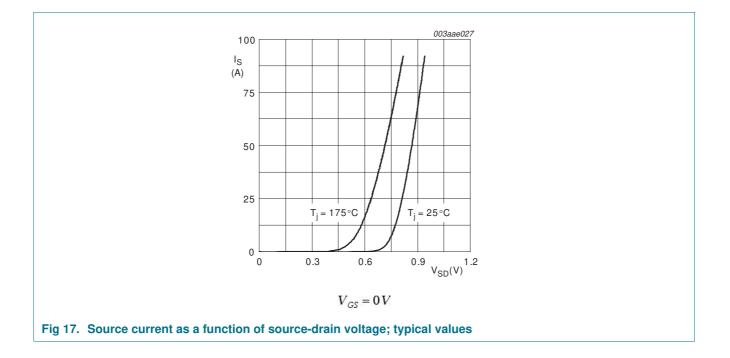
PSMN9R5-100BS



PSMN9R5-100BS



PSMN9R5-100BS



N-channel 100 V 9.6 m Ω standard level MOSFET in D2PAK

7. Package outline

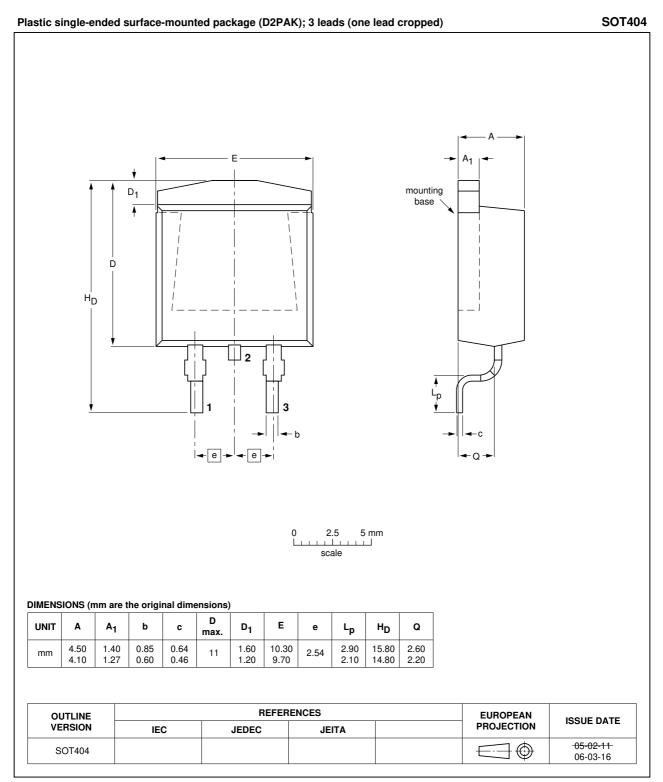


Fig 18. Package outline SOT404 (D2PAK)

N-channel 100 V 9.6 mΩ standard level MOSFET in D2PAK

8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN9R5-100BS v.2	20120302	Product data sheet	-	PSMN9R5-100BS v.1
Modifications:	 Status changed f 	rom objective to product.		
	 Various changes 	to content.		
PSMN9R5-100BS v.1	20111025	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

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